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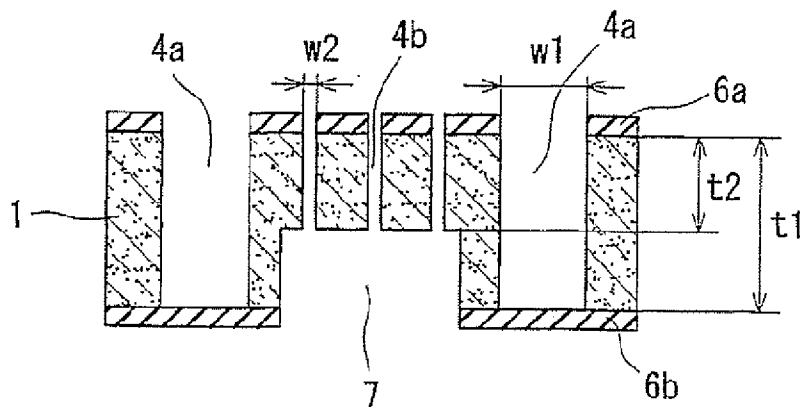
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(54) Title: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE



(57) Abstract: Disclosed is  
a method of manufacturing a  
semiconductor device. In this  
method, a concave portion (7)  
is formed in one surface in the  
thickness direction of a primary  
base plate (1) comprising a  
semiconductor substrate with a  
relatively large thickness dimension.  
Then, through holes (4a, 4b) are  
formed by a reactive-ion etching  
process using as a mask an opening  
(8) formed in an oxide film (6a)  
provided on the other surface in the  
thickness direction of the primary  
base plate (1). The opening (8)  
has a narrow width in a region

corresponding to the concave portion (7) and a wide width in the remaining region. Thus, respective times necessary for the  
wide-width through-hole (4a) to penetrate through the primary base plate (1) and necessary for the narrow-width through-hole (4b)  
to reach a bottom surface of the concave portion (7) can be approximately equalized to complete the common etching process of  
the wide-width through-hole (4a) and the narrow-width through-hole (4b) approximately simultaneously.